

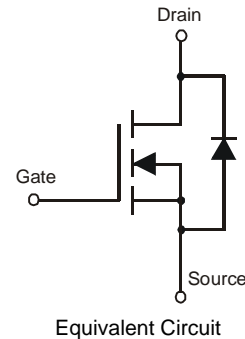
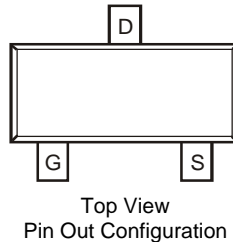
## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	$I_D \max$ $T_A = 25^\circ\text{C}$
60V	3Ω @ $V_{GS} = 10\text{V}$	300mA

## Description and Applications

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Power Management Functions



## Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- **Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 1, 2 and 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

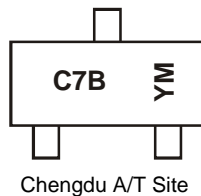
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

## Ordering Information (Note 4)

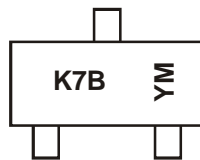
Part Number	Case	Packaging
2N7002E-7-F	SOT23	3000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free
  2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
  3. Product manufactured with Date Code V12 (week 50, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V12 are built with Non-Green Molding Compound and may contain Halogens or  $\text{Sb}_2\text{O}_3$  Fire Retardants
  4. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



Chengdu A/T Site



Shanghai A/T Site

- K = SAT (Shanghai Assembly/ Test site)
- C = CAT (Chengdu Assembly/ Test site)
- 7B = Product Type Marking Code
- YM = Date Code Marking
- Y = Year (ex: N = 2002)
- M = Month (ex: 9 = September)

### Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	P	R	S	T	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Drain-Gate Voltage R <sub>GS</sub> ≤ 1.0MΩ			V <sub>DGR</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
				±40	
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	250	mA
		T <sub>A</sub> = 70°C		200	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	300	mA
		T <sub>A</sub> = 70°C		240	
Maximum Body Diode Forward Current (Note 6)			I <sub>S</sub>	500	mA
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I <sub>DM</sub>	800	mA

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P <sub>D</sub>	370	mW
	(Note 6)		540	
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>θJA</sub>	348	°C/W
	(Note 6)		241	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>θJC</sub>	91	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	70	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0 500	μA	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10	nA	V <sub>GS</sub> = ±15V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.6 2.0	3 4	Ω	@ T <sub>J</sub> = 25°C V <sub>GS</sub> = 10V, I <sub>D</sub> = 250mA V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 200mA
On-State Drain Current	I <sub>D(ON)</sub>	0.8	1.0	—	A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance	g <sub>FS</sub>	80	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	22	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	11	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.0	5.0	pF	
Gate resistance	R <sub>g</sub>	—	120	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	223	—	pC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	—	82	—	pC	
Gate-Drain Charge	Q <sub>gd</sub>	—	178	—	pC	
<b>SWITCHING CHARACTERISTICS (Note 8)</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	7.0	20	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.2A, R <sub>L</sub> = 150Ω, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25Ω
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	11	20	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout
  - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

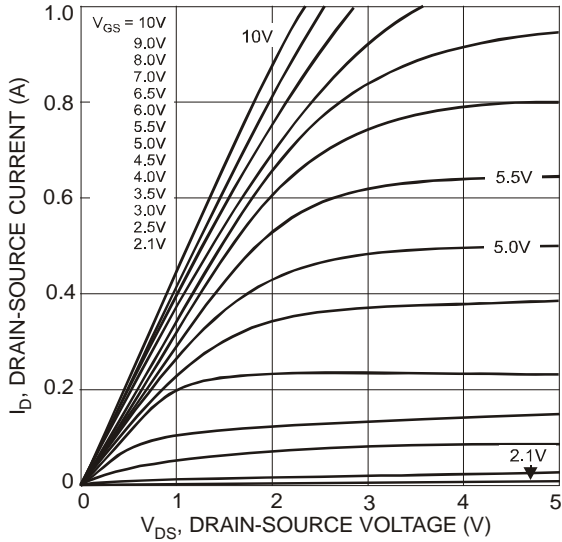


Fig. 1 On-Region Characteristics

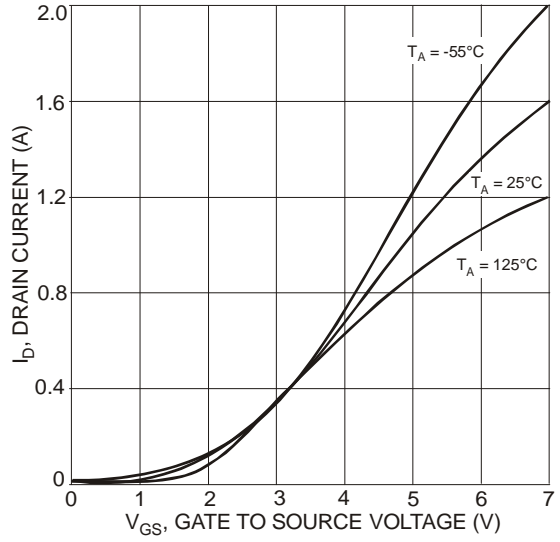


Fig. 2 Drain Current vs. Gate-Source Voltage

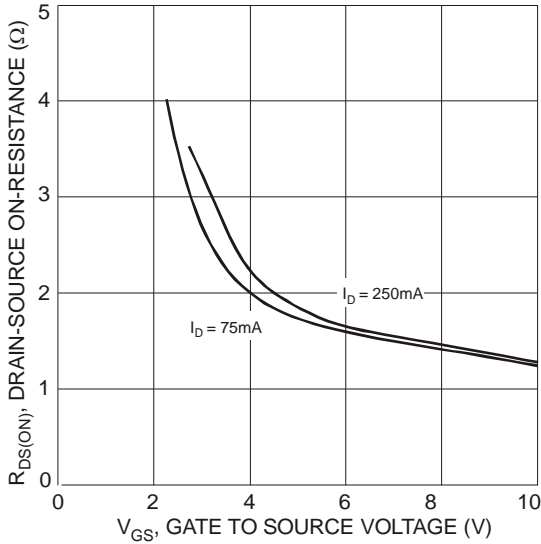


Fig. 3 On Resistance vs. Gate-Source Voltage

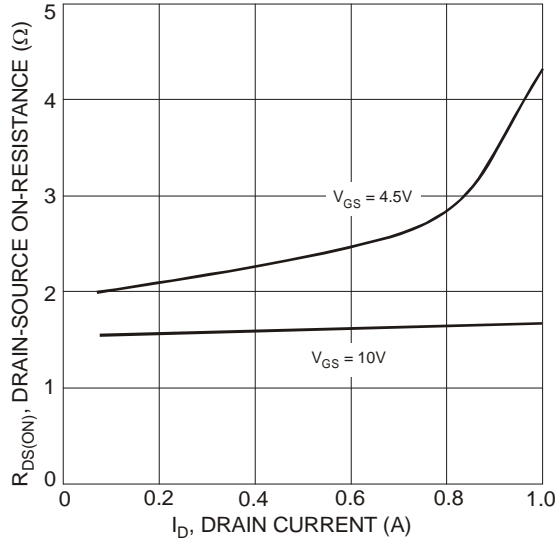


Fig. 4 On Resistance vs. Drain Current

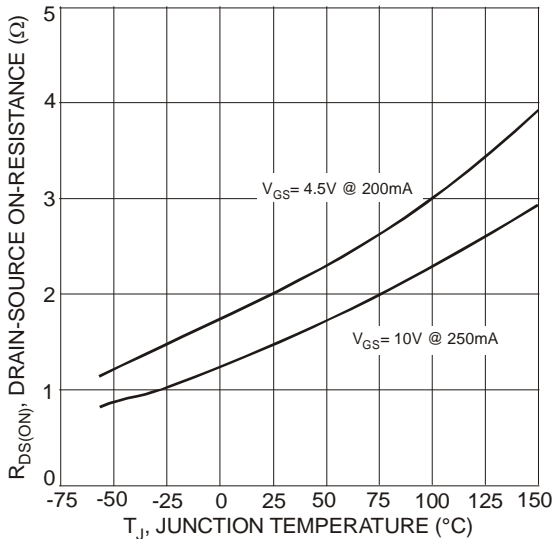


Fig. 5 On-Resistance vs. Junction Temperature

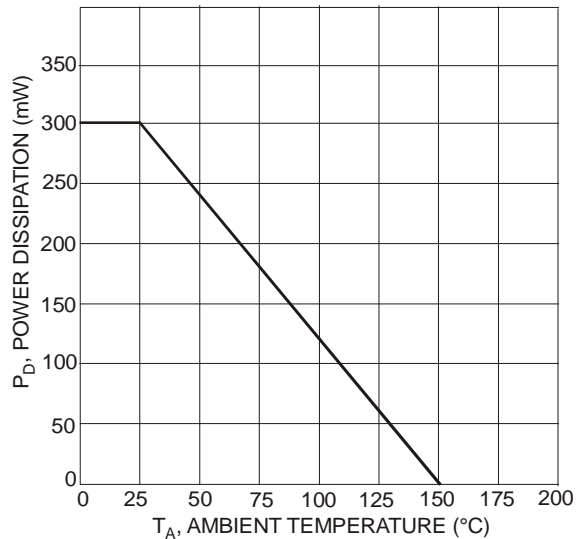
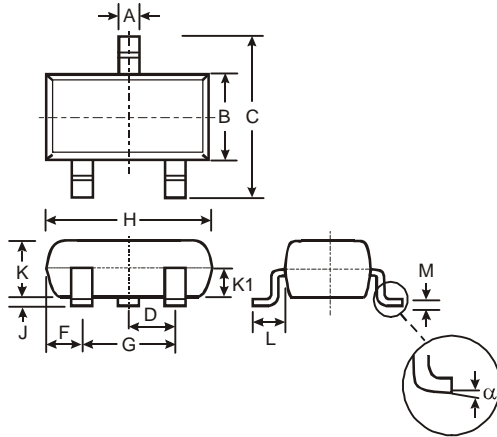


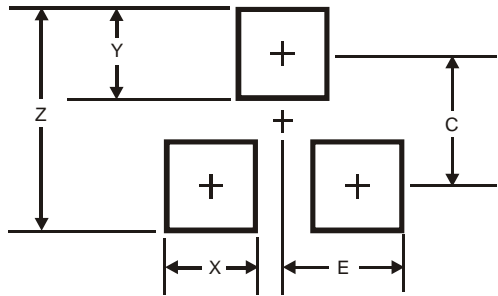
Fig. 6 Max Power Dissipation vs. Ambient Temperature

**Package Outline Dimensions**



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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